





Texas Instruments

SN74LVC1G3157 SCES424M – JANUARY 2003 – REVISED AUGUST 2022

SN74LVC1G3157 Single-Pole Double-Throw Analog Switch

1 Features

- ESD protection exceeds JESD 22
 - 2000-V Human Body Model (A114-A)
 - 1000-V Charged-Device Model (C101)
- 1.65-V to 5.5-V V_{CC} operation
- Qualified for 125°C operation
- Specified break-before-make switching
- Rail-to-rail signal handling
- Operating frequency typically 340 MHz at room temperature
- High speed, typically 0.5 ns (V_{CC} = 3 V, C_L = 50 pF)
- Low ON-state resistance, typically ≉6 Ω (V_{CC} = 4.5 V)
- Latch-up performance exceeds 100 mA Per JESD 78, class II

2 Applications

- Wearables and mobile devices
- Portable computing
- Internet of things (IoT)
- Audio signal routing
- Remote radio unit
- Portable medical equipment
- Surveillance
- Home automation
- I2C/SPI/UART bus multiplexing
- Wireless charging

3 Description

This single channel single-pole double-throw (SPDT) analog switch is designed for 1.65-V to 5.5-V $\rm V_{\rm CC}$ operation.

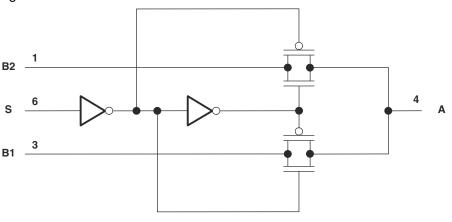
The SN74LVC1G3157 device can handle both analog and digital signals. The SN74LVC1G3157 device permits signals with amplitudes of up to V_{CC} (peak) to be transmitted in either direction.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)	
	SOT-23 (DBV) (6)	2.90 mm × 1.60 mm	
	SC70 (DCK) (6)	2.00 mm × 1.25 mm	
SN74LVC1G3157	SOT (DRL) (6)	1.60 mm × 1.20 mm	
	SON (DRY) (6)	1.45 mm × 1.00 mm	
	DSBGA (YZP) (6)	1.41 mm × 0.91 mm	
	SON (DSF) (6)	1.00 mm × 1.00 mm	
	X2SON (DTB) (6)	0.80 mm × 1.00 mm	

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Simplified Schematic



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	hanges from Revision L (May 2017) to Revision M (August 2022)	Page
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1
•	Updated the Pin Configuration and Functions section	4
•	Updated the equation in the Detailed Design Procedure section	18

С	hanges from Revision K (January 2017) to Revision L (May 2017)	Page
•	Deleted Feature "Useful for Both Analog and Digital Applications"	1
•	Deleted Feature "High Degree of Linearity"	
•	Changed the first sentence of the Description From: "This single-pole double-throw (SPDT)" To: "This	
	channel single pole double-throw (SPDT)"	1
•	Added the X2SON (DTB) package to the Device Information	
•	Added the X2SON (DTB) Package, to the Pin Configuration and Functions	4
•	Changed II/O To: II/OK for I/O port diode current in the Absolute Maximum Ratings	6
•	Added the DTB (X2SON) package to the Thermal Information table	7
•	Changed Note 1 and Note 2 n the Analog Switch Characteristics table	9
•	Deleted Note 3 "Specified by design" from the Analog Switch Characteristics tables	9
•	Deleted Note 4 "Specified by design" from the Switch Characteristics 85°C tables	10
•	Deleted Note 4 "Specified by design" from the Switch Characteristics 125°C tables	10
•	Changed Figure 7-2, From: SW1 = V_{IL} to SW1 = V_{IH} , From: SW2 = V_{IH} to: SW2 = V_{IL}	11
•	Changed Figure 7-5	
•	Added a series 50-Ω resistor on B1 in Figure 7-6	
•	Changed Figure 7-7	

Changes from Revision J (June 2016) to Revision K (January 2017)

•	Added new applications to Applications section	1	1
	Added Operating free-air temperature, T _A for BGA and all other packages in <i>Recommended Operating</i>		
	Conditions	7	7
•	Added 125°C data to Electrical Characteristics table.	8	3
•	Added 85°C to title to differentiate from new 125°C Switching Characteristics section.	10)

Page



www.ti.com	SCES424M – JANUARY 2003 – REVISED AUGUST 2022
Added 125°C Switching Characteristics section and data	a10
Changes from Revision I (June 2015) to Revision J (Jun	ne 2016) Page
Deleted 200-V Machine Model (A115-A) from Features .	1
 Changed <i>Feature</i> From: "Operating Frequency Typically Frequency Typically 340 MHz at Room Temperature" 	1
 Updated <i>Device Information</i> table Updated pinout images for all Packages 	I
 Added temperature ranges for Storage temperature, T_{st} 	
 Ratings Changed MAX value ±1 to ±0.1 for I_{off} and I_{IN} in <i>Electric</i> 	
 Added Receiving Notification of Documentation Updates 	
Changes from Revision H (May 2012) to Revision I (Jun	e 2015) Page
Added Device Information table, Pin Configuration and I	Functions section. ESD Ratings table. Feature
Description section, Device Functional Modes, Applicati	
Recommendations section, Layout section, Device and	
Packaging, and Orderable Information section	
Updated <i>Features</i>	
•	
Changes from Revision G (September 2011) to Revision	n H (May 2012) Page

			<u> </u>
•	Changed YZP with correct pin labels.		ŧ
•	Added Thermal Information table	7	7
•	Changed to correct Pin Label "S"	8	3
	•		

5 Pin Configuration and Functions

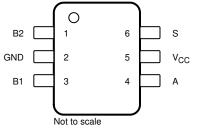
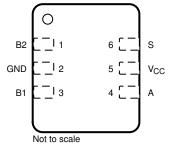
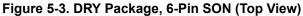
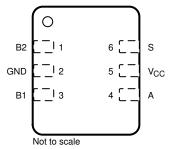
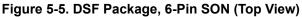


Figure 5-1. DBV Package, 6-Pin SOT-23 (Top View)









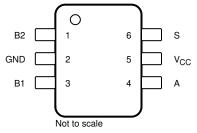
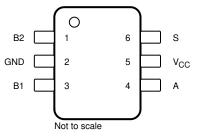


Figure 5-2. DCK Package, 6-Pin SC70 (Top View)





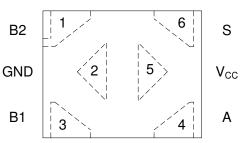


Figure 5-6. DTB Package, 6-Pin X2SON (Top View)

Table 5-1. Pin Functions

PIN				
NAME	SOT-23, SC70, SON, X2SON, or SOT	TYPE ⁽¹⁾	DESCRIPTION	
B2	1	I/O	Switch I/O. Set S high to enable.	
GND	2	Р	Ground	
B1	3	I/O	Switch I/O. Set S low to enable.	
A	4	I/O	Common terminal	
V _{CC}	5	Р	P Power supply	
S	6	I	Select	

(1) I = input, O = output, P = power



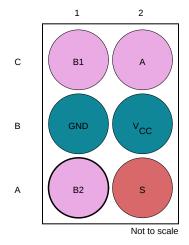


Figure 5-7. YZP Package, 6-Pin DSBGA (Bottom View)

Legend			
Input	Input or Output		
Power			

Table 5-2. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION	
NO.				
A1	B2	I/O	Switch I/O. Set S high to enable.	
A2	S	I	Select	
B1	GND	Р	Ground	
B2	V _{CC}	Р	Power supply	
C1	B1	I/O	Switch I/O. Set S low to enable.	
C2	A	I/O	Common terminal	

(1) I = input, O = output, P = power



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage ⁽²⁾		-0.5	6.5	V
V _{IN}	Control input voltage ^{(2) (3)}		-0.5	6.5	V
V _{I/O}	Switch I/O voltage ^{(2) (3) (4) (5)}		-0.5	V _{CC} + 0.5	V
I _{IK}	Control input clamp current	V _{IN} < 0		-50	mA
I _{I/OK}	I/O port diode current	$V_{I/O}$ < 0 or $V_{I/O}$ > V_{CC}		±50	mA
I _{I/O}	On-state switch current ⁽⁶⁾	$V_{I/O} = 0$ to V_{CC}		±128	mA
	Continuous current through V_{CC} or GND			±100	mA
TJ	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to ground unless otherwise specified.

(3) The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

(4) This value is limited to 5.5 V maximum.

(5) V_I , V_O , V_A , and V_{Bn} are used to denote specific conditions for $V_{I/O}$.

(6) I_{I} , I_{O} , I_{A} , and I_{Bn} are used to denote specific conditions for $I_{I/O}$.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
V(ESD)		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	v

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		1.65	5.5	V
V _{I/O}	Switch input or output voltage		0	V _{CC}	V
V _{IN}	Control input voltage		0	5.5	V
V	Lligh lovel input veltage, central input	V _{CC} = 1.65 V to 1.95 V	V _{CC} × 0.75		V
VIH	High-level input voltage, control input	V_{CC} = 2.3 V to 5.5 V	V _{CC} × 0.7		v
V		V _{CC} = 1.65 V to 1.95 V		V _{CC} × 0.25	V
VIL	Low-level input voltage, control input	V_{CC} = 2.3 V to 5.5 V		V _{CC} × 0.3	v
		V _{CC} = 1.65 V to 1.95 V		20	
A.L.A		V_{CC} = 2.3 V to 2.7 V		20	··· • / /
Δt/Δv	Input transition rise or fall rate	V _{CC} = 3 V to 3.6 V		10	ns/V
		$V_{C\ C}$ = 4.5 V to 5.5 V		10	
		BGA package (YZP)	-40	85	°C
T _A	Operating free-air temperature	All other packages (DBV, DCK, DRL, DRY, DSF)	-40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See the TI application report, *Implications of Slow or Floating CMOS Inputs* (SCBA004).

6.4 Thermal Information

				SN74LVC1	G3157			
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DCK (SC70)	DRL (SOT)	DRY (SON)	DTB (X2SON)	YZP (DSBGA)	UNIT
		6 PINS	6 PINS	6 PINS	6 PINS	6 PINS	6 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	234.9	269.5	244.1	284.2	324.5	129.4	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	150.4	189.5	112.5	138.6	150.5	1.9	°C/W
R _{θJB}	Junction-to-board thermal resistance	86.4	84.7	109.9	170.9	239.0	40.0	°C/W
τιΨ	Junction-to-top characterization parameter	60.8	62.7	9.3	13.7	17.2	0.6	°C/W
Ψјв	Junction-to-board characterization parameter	86.1	84.0	109.3	167.9	238.3	40.2	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	n/a	n/a	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER			TEST CONDITION	IS .	V	T _A =	-40 to 85	°C	T _A = -40 to 125°C			UNIT
	PARAMETER			TEST CONDITION	15	V _{cc}	MIN	TYP ⁽¹⁾	MAX	MIN	TYP ⁽¹⁾	MAX	UNI
				V ₁ = 0 V	I _O = 4 mA	- 1.65 V		11	20		11	20	
				V _I = 1.65 V	I _O = -4 mA	1.05 V		15	50		15	50	I
				V ₁ = 0 V	I _O = 8 mA	2.3 V		8	12		8	12	
				V _I = 2.3 V	I _O = -8 mA	2.3 V		11	30		11	30	
on	ON-state switch resistance ⁽²⁾		See Figure 6-1 and Figure 7-1	V _I = 0 V	I _O = 24 mA	- 3 V		7	9		7	9	Ω
			, , , , , , , , , , , , , , , , , , ,	V _I = 3 V	I _O = -24 mA	30		9	20		9	20	
				V _I = 0 V	I _O = 30 mA			6	7		6	7	
				V _I = 2.4 V	I _O = -30 mA	4.5 V		7	12		7	12	
				V _I = 4.5 V	I _O = -30 mA			7	15		7	15	
				•	I _A = -4 mA	1.65 V			140			140	
	ON-state switch resistance o	ver	$0 \le V_{Bn} \le V_{CC}$		I _A = -8 mA	2.3 V			45			45	Ω
range	signal range ^{(2) (3)}		(see Figure 6-1 a	nd Figure 7-1)	I _A = -24 mA	3 V			18			18	1
					I _A = -30 mA	4.5 V			10			10	1
				V _{Bn} = 1.15 V	I _A = -4 mA	1.65 V		0.5			0.5		
	Difference of ON-state			V _{Bn} = 1.6 V	I _A = -8 mA	2.3 V		0.1			0.3		c
\r _{on}	resistance between switches	(2) (4) (5)	See Figure 7-1	V _{Bn} = 2.1 V	I _A = -24 mA	3 V		0.1			0.3		L.
				V _{Bn} = 3.15 V	I _A = -30 mA	4.5 V		0.1			0.2		
					I _A = -4 mA	1.65 V		110			110		
	ON resistance flatness ⁽²⁾ (4) (6)			I _A = -8 mA	2.3 V		26			40		c
on(flat)	ON resistance natness	0)	$0 \le V_{Bn} \le V_{CC}$		I _A = -24 mA	3 V		9			10		L.
					I _A = -30 mA	4.5 V		4			5		
off ⁽⁷⁾	OFF-state switch leakage cu	rrant	$0 \le V_{I}, V_{O} \le V_{CC}$			1.65 V to			±1			±1	μ
off	OFF-State Switch leakage cu	nem	(see Figure 7-2)			5.5 V		±0.05	±0.1 ⁽¹⁾		±0.05	±0.1	μ/
	ON state switch lookens sum		V _I = V _{CC} or GND,	V _O = Open		5.5 V			±1			±1	
S(on)	ON-state switch leakage curr	ent	(see Figure 7-3)			5.5 V			±0.1 ⁽¹⁾			±0.1 ⁽¹⁾	μı
	Control input sumant					0 V to 5.5			±1			±1	·
IN	Control input current		$0 \le V_{IN} \le V_{CC}$			V		±0.05	±0.1 ⁽¹⁾		±0.05	±0.1	μ
cc	Supply current		$S = V_{CC} \text{ or } GND$			5.5 V		1	10			35	μ
I _{CC}	Supply-current change		$S = V_{CC} - 0.6 V$			5.5 V			500			500	μ
2 _i	Control input capacitance	S				5 V		2.7			2.7		pl
Pio(off)	Switch input/output capacitance	Bn				5 V		5.2			5.2		pf
<u>`</u>	Switch input/output	Bn				5.1		17.3			17.3		
Cio(on)	capacitance	А	1			5 V -		17.3			17.3		pł

(1) T_A = 25°C

Measured by the voltage drop between I/O pins at the indicated current through the switch. ON-state resistance is determined by the (2) lower of the voltages on the two (A or B) ports.

(3) Specified by design

 $\Delta r_{on} = r_{on(max)} - r_{on(min)}$ measured at identical V_{CC}, temperature, and voltage levels This parameter is characterized, but not production tested. (4)

(5)

Flatness is defined as the difference between the maximum and minimum values of on-state resistance over the specified range of (6) conditions.

(7) I_{off} is the same as $I_{\text{S(off)}}$ (off-state switch leakage current).



6.6 Analog Switch Characteristics

T_A = 25°C

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _{cc}	ТҮР	UNIT	
				1.65 V	340		
Frequency response ⁽¹⁾	A or Bn	Bn or A	$R_{L} = 50 \Omega$, $f_{in} = sine wave$	2.3 V	340	MHz	
(switch on)	AOLPH	BILOFA	(see Figure 7-5)	3 V	340	MILZ	
				4.5 V	340		
				1.65 V	-54		
Crosstalk ⁽²⁾	D1 or D2	D2 or D1	$R_{L} = 50 \Omega$, $f_{in} = 10 MHz$ (sine wave)	2.3 V	-54	dB	
(between switches)	B1 or B2 B2 or B1 (see Figure 7-6)		(see Figure 7-6)	3 V	-54	aв	
				4.5 V	-54		
				1.65 V	-57		
Feed through attenuation ⁽²⁾	A or Bn	Bn or A	$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	-57	dB	
(switch off)	AOLPH		f _{in} = 10 MHz (sine wave) (see Figure 7-7)	3 V	-57		
				4.5 V	-57		
Charge injection	ŝ	•	C _L = 0.1 nF, R _L = 1 MΩ	3.3 V	3		
Charge injection	S	A	(see Figure 7-8)	5 V	7	рС	
				1.65 V	0.1%		
Total harmonic distortion	A or Dr	Dr. er A	$V_{I} = 0.5 V_{p-p}, R_{L} = 600 \Omega,$ f _{in} = 600 Hz to 20 kHz (sine wave)	2.3 V	0.025%		
	A or Bn	Bn or A	(see Figure 7-9)	3 V	0.015%		
				4.5 V	0.01%		



6.7 Switching Characteristics 85°C

 $T_A = -40$ to +85°C (see Figure 7-4 and)Figure 7-10

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1			V _{CC} = 2.5 V ± 0.2 V		3.3 V 3 V	V _{CC} = 5 V ± 0.5 V		UNIT
		(001201)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd} ⁽¹⁾	A or Bn	Bn or A		2		1.2		0.8		0.3	ns
t _{en} ⁽²⁾	S	Bn	7	24	3.5	14	2.5	7.6	1.7	5.7	20
t _{dis} ⁽³⁾		DII	3	13	2	7.5	1.5	5.3	0.8	3.8	ns
t _{B-M}			0.5		0.5		0.5		0.5		ns

(1) t_{pd} is the slower of t_{PLL} or t_{PHL}. The propagation delay is calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance when driven by an ideal voltage source (zero output impedance).

(2) t_{en} is the slower of t_{PZL} or t_{PZH} .

(3) t_{dis} is the slower of t_{PLZ} or t_{PHZ} .

6.8 Switching Characteristics 125°C

$T_A = -40$ to +125°C (see Figure 7-4 and Figure 7-10)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1		V _{CC} = 2 ± 0.2		V _{CC} = : ± 0.3		V _{CC} = ± 0.5		UNIT
		(001201)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd} ⁽¹⁾	A or Bn	Bn or A		2		1.2		0.8		0.5	ns
t _{en} ⁽²⁾	S	Bn	1	24.5	1	14.5	2.5	8	1.7	6	20
t _{dis} ⁽³⁾	5	DII	2.5	13.5	2	8	1.5	5.5	0.8	4	ns
t _{B-M}			0.5		0.5		0.5		0.5		ns

6.9 Typical Characteristics

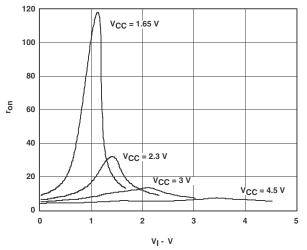


Figure 6-1. Typical r_{on} as a Function of Input Voltage (V_I) for V_I = 0 to V_{CC}



7 Parameter Measurement Information

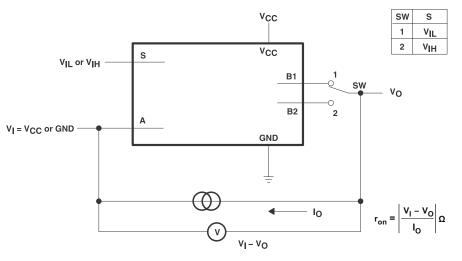
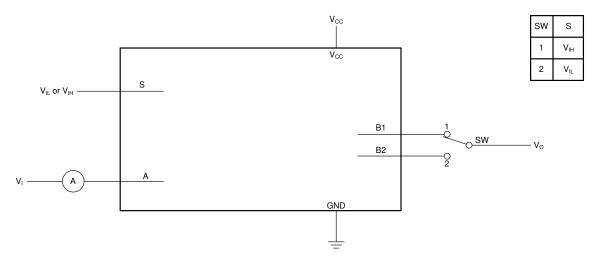
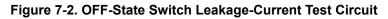
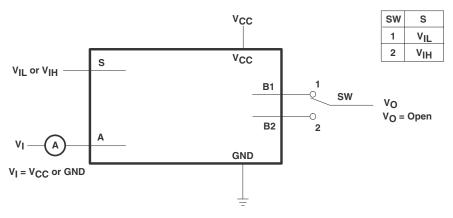


Figure 7-1. ON-State Resistance Test Circuit



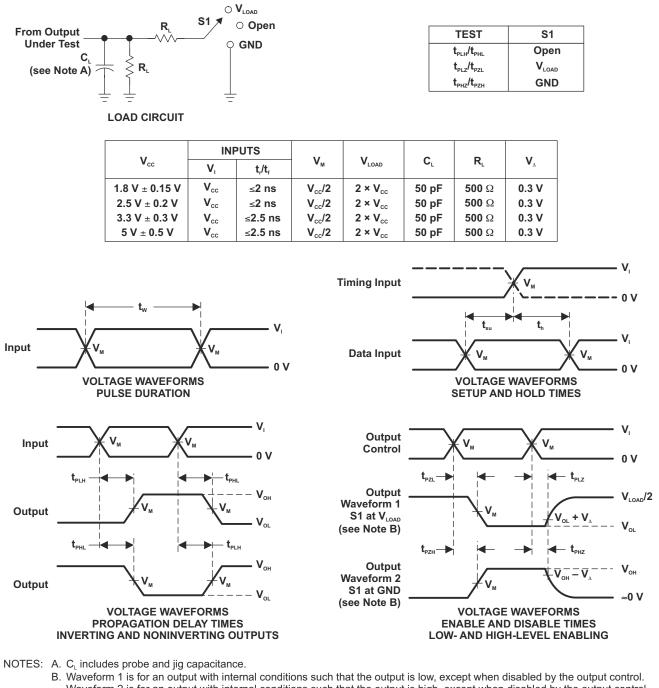
 $\begin{array}{l} Condition \ 1: \ V_I = GND, \ V_O = V_{CC} \\ Condition \ 2: \ V_I = V_{CC}, \ V_O = GND \end{array}$



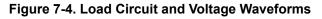






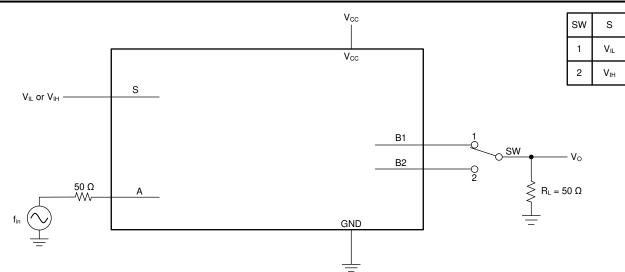


- Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_o = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. $t_{\mbox{\tiny PLZ}}$ and $t_{\mbox{\tiny PHZ}}$ are the same as $t_{\mbox{\tiny dis}}.$
- F. $t_{\mbox{\tiny PZL}}$ and $t_{\mbox{\tiny PZH}}$ are the same as $t_{\mbox{\tiny en}}.$
- G. $t_{\mbox{\tiny PLH}}$ and $t_{\mbox{\tiny PHL}}$ are the same as $t_{\mbox{\tiny pd}}^{\mbox{\tiny on}}$
- H. All parameters and waveforms are not applicable to all devices.

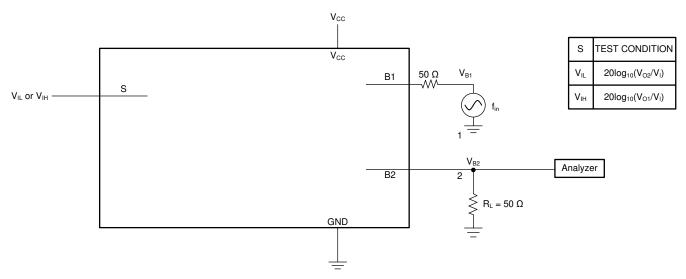




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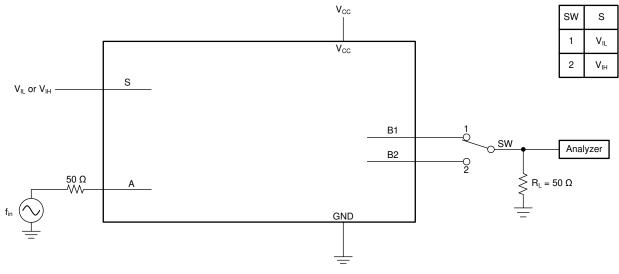


Figure 7-7. Feed Through

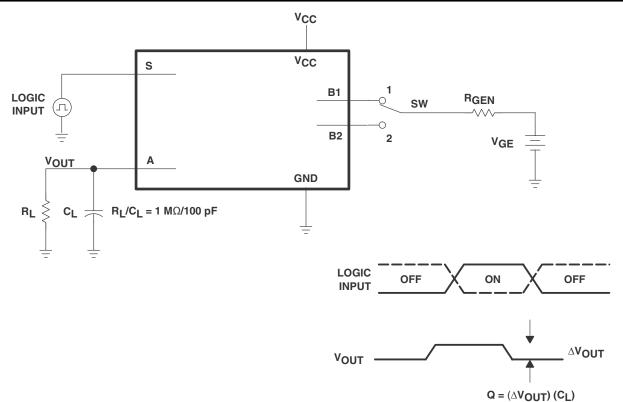


Figure 7-8. Charge-Injection Test

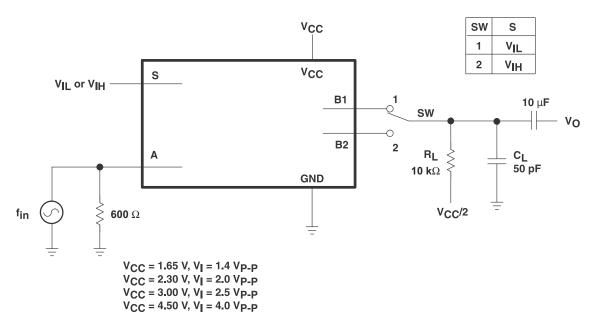


Figure 7-9. Total Harmonic Distortion



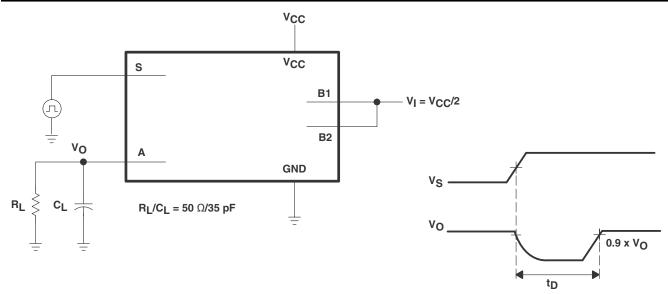


Figure 7-10. Break-Before-Make Internal Timing



8 Detailed Description

8.1 Overview

The SN74LVC1G3157 device is a single-pole double-throw (SPDT) analog switch designed for 1.65-V to 5.5-V V_{CC} operation. The SN74LVC1G3157 device can handle analog and digital signals. The device permits signals with amplitudes of up to V_{CC} (peak) to be transmitted in either direction.

8.2 Functional Block Diagram

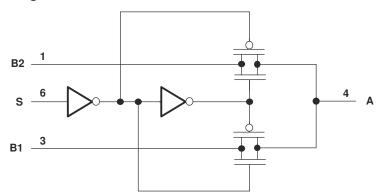


Figure 8-1. Logic Diagram (Positive Logic)

8.3 Feature Description

The 1.65-V to 5.5-V supply operation allows the device to function in many different systems comprised of different logic levels, allowing rail-to-rail signal switching. Either the B1 channel or the B2 channel is activated depending upon the control input. If the control input is low, B1 channel is selected. If the control input is high, B2 channel is selected.

8.4 Device Functional Modes

Table 8-1 lists the ON channel when one of the control inputs is selected.

Table 8-1. Function Table									
CONTROL ON INPUTS CHANNEL									
L	B1								
Н	B2								

16 Submit Document Feedback



9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC1G3157 SPDT analog switch is flexible enough for use in a variety of circuits such as analog audio routing, power-up monitor, memory sharing, and so on. For details on the applications, see SN74LVC1G3157 and SN74LVC2G53 SPDT Analog Switches.

9.2 Typical Application

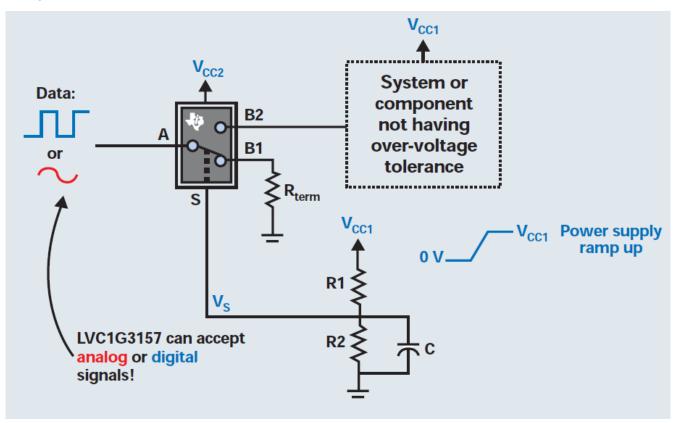


Figure 9-1. Typical Application Schematic

9.2.1 Design Requirements

The inputs can be analog or digital, but TI recommends waiting until V_{CC} has ramped to a level in Section 6.3 before applying any signals. Appropriate termination resistors should be used depending on the type of signal and specification. The Select pin should not be left floating; either pull up or pull down with a resistor that can be overdriven by a GPIO.



9.2.2 Detailed Design Procedure

Using this circuit idea, a system designer can ensure a component or subsystem power has ramped up before allowing signals to be applied to its input. This is useful for integrated circuits that do not have overvoltage tolerant inputs. The basic idea uses a resistor divider on the VCC1 power rail, which is ramping up. The RC time constant of the resistor divider further delays the voltage ramp on the select pin of the SPDT bus switch. By carefully selecting values for R1, R2, and C, it is possible to ensure that VCC1 will reach its nominal value before the path from A to B2 is established, thus preventing a signal being present on an I/O before the device/ system is powered up. To ensure the minimum desired delay is achieved, the designer should use Equation 1 to calculate the time required from a transition from ground (0 V) to half the supply voltage (VCC1/2).

$$\operatorname{Set}\left(\frac{R2}{R1+R2} \times \operatorname{VCC1} > \operatorname{VIH}\right)$$
 of the select pin

(1)

Choose Rs and C to achieve the desired delay.

When V_S goes high, the signal will be passed.

9.2.3 Application Curve

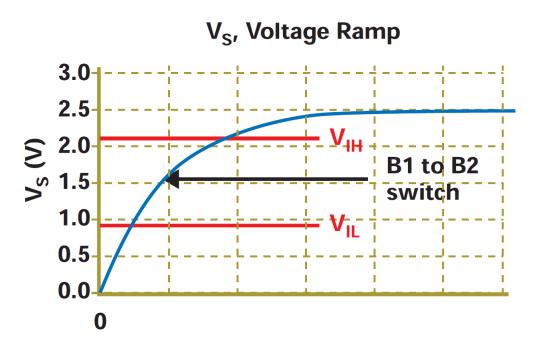


Figure 9-2. V_S Voltage Ramp



10 Power Supply Recommendations

Most systems have a common 3.3-V or 5-V rail that can supply the V_{CC} pin of this device. If this is not available, a Switch-Mode-Power-Supply (SMPS) or a Linear Dropout Regulator (LDO) can be used to provide supply to this device from another voltage rail.

11 Layout

11.1 Layout Guidelines

TI recommends keeping signal lines as short as possible. TI also recommends incorporating microstrip or stripline techniques when signal lines are greater than 1 inch in length. These traces must be designed with a characteristic impedance of either 50 Ω or 75 Ω , as required by the application. Do not place this device too close to high-voltage switching components, as they may interfere with the device.

11.2 Layout Example

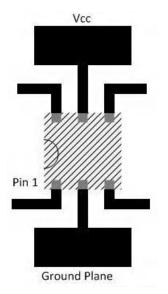


Figure 11-1. Recommended Layout Example



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, Implications of Slow or Floating CMOS Inputs
- Texas Instruments, SN74LVC1G3157 and SN74LVC2G53 SPDT Analog Switches

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1G3157DBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(CC55, CC5F, CC5K, CC5R) CC5S	Samples
SN74LVC1G3157DCK3	OBSOLETE	SC70	DCK	6		TBD	Call TI	Call TI	-40 to 125	C5Z	
SN74LVC1G3157DCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C55, C5F, C5J, C5 R)	Samples
SN74LVC1G3157DRLR	ACTIVE	SOT-5X3	DRL	6	4000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(C57, C5R)	Samples
SN74LVC1G3157DRY2	OBSOLETE	SON	DRY	6		TBD	Call TI	Call TI	-40 to 125	C5	
SN74LVC1G3157DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C5	Samples
SN74LVC1G3157DSFR	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	C5	Samples
SN74LVC1G3157DTBR	ACTIVE	X2SON	DTB	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	7X	Samples
SN74LVC1G3157YZPR	ACTIVE	DSBGA	YZP	6	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C5N	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <= 1000ppm threshold. Antimony trioxide based flame retardants must also meet the <= 1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



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PACKAGE OPTION ADDENDUM

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC1G3157 :

Automotive : SN74LVC1G3157-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



Texas

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G3157DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G3157DCKR	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G3157DRLR	SOT-5X3	DRL	6	4000	180.0	8.4	2.0	1.8	0.75	4.0	8.0	Q3
SN74LVC1G3157DRYR	SON	DRY	6	5000	180.0	9.5	1.2	1.65	0.7	4.0	8.0	Q1
SN74LVC1G3157DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G3157DSFR	SON	DSF	6	5000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC1G3157DTBR	X2SON	DTB	6	3000	180.0	9.5	0.94	1.13	0.41	2.0	8.0	Q2
SN74LVC1G3157YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



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PACKAGE MATERIALS INFORMATION

14-Dec-2024



All ultrensions are norminal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G3157DBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0
SN74LVC1G3157DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC1G3157DRLR	SOT-5X3	DRL	6	4000	210.0	185.0	35.0
SN74LVC1G3157DRYR	SON	DRY	6	5000	189.0	185.0	36.0
SN74LVC1G3157DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC1G3157DSFR	SON	DSF	6	5000	210.0	185.0	35.0
SN74LVC1G3157DTBR	X2SON	DTB	6	3000	189.0	185.0	36.0
SN74LVC1G3157YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0

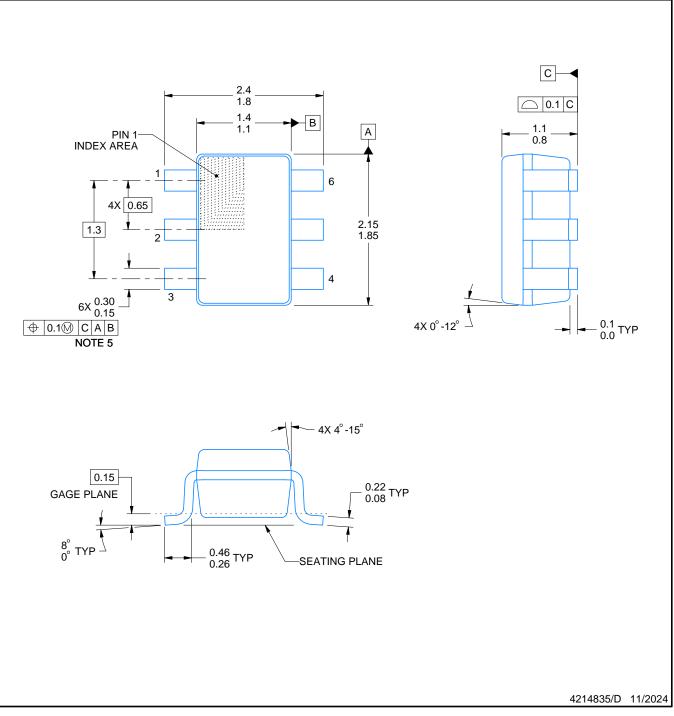
DCK0006A



PACKAGE OUTLINE

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing an integration of a constraint of the minimeters. Any dimensions in parentnesis are for reference only. Dimensioning and to per ASME Y14.5M.
 This drawing is subject to change without notice.
 Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 Falls within JEDEC MO-203 variation AB.



DCK0006A

EXAMPLE BOARD LAYOUT

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

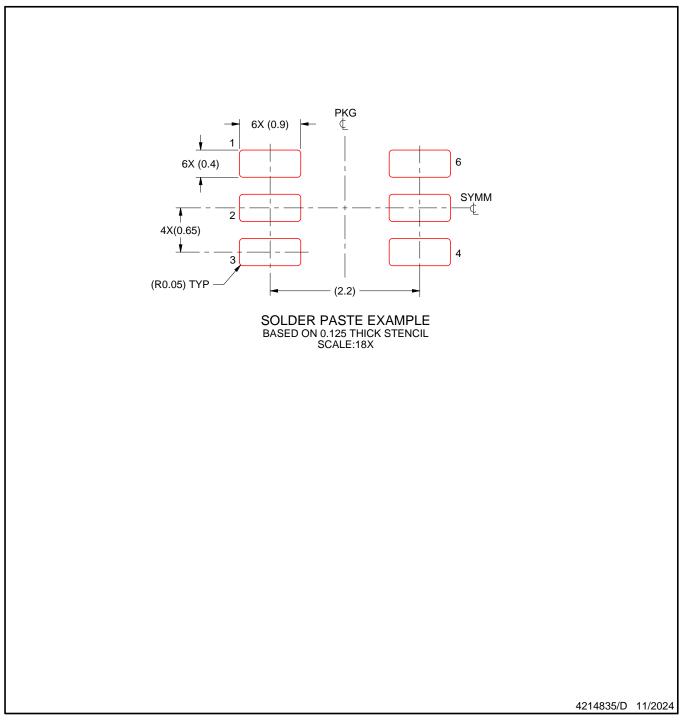


DCK0006A

EXAMPLE STENCIL DESIGN

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Board assembly site may have different recommendations for stencil design.



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

GENERIC PACKAGE VIEW

USON - 0.6 mm max height PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



4207181/G

DRY0006A



PACKAGE OUTLINE

USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.



DRY0006A

EXAMPLE BOARD LAYOUT

USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).



DRY0006A

EXAMPLE STENCIL DESIGN

USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



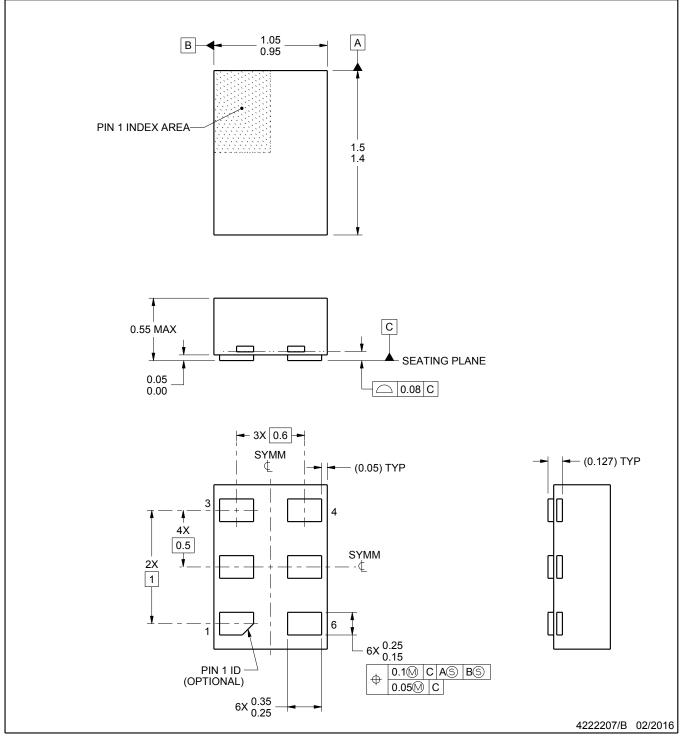
DRY0006B



PACKAGE OUTLINE

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.

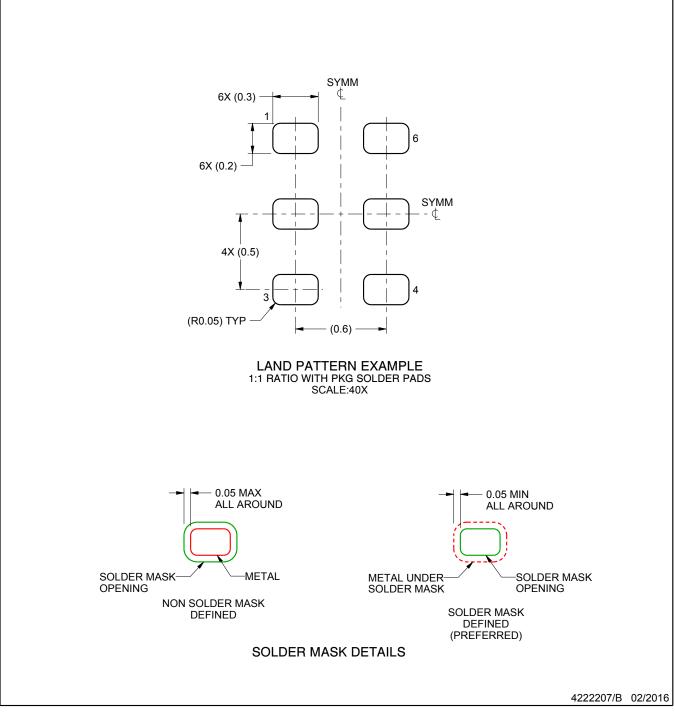


DRY0006B

EXAMPLE BOARD LAYOUT

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).

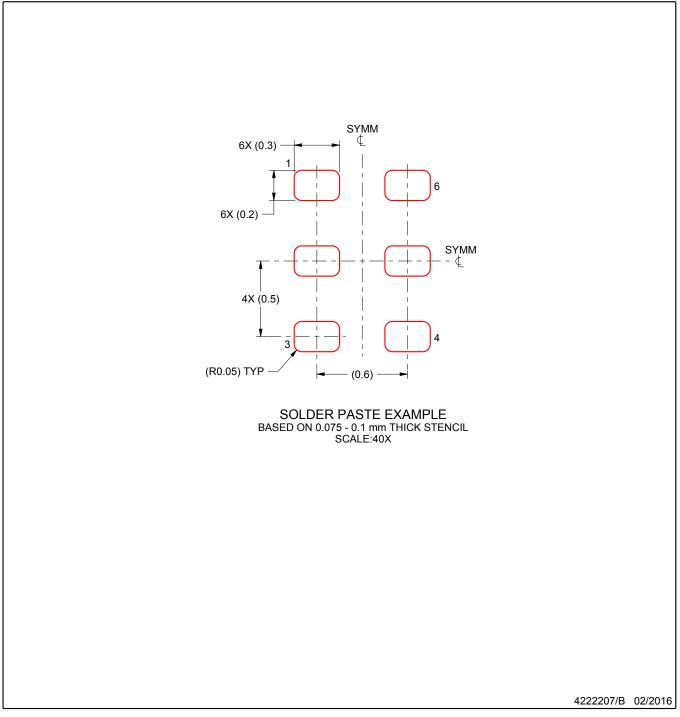


DRY0006B

EXAMPLE STENCIL DESIGN

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



DSF0006A



PACKAGE OUTLINE

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing Per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC registration MO-287, variation X2AAF.



DSF0006A

EXAMPLE BOARD LAYOUT

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



DSF0006A

EXAMPLE STENCIL DESIGN

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



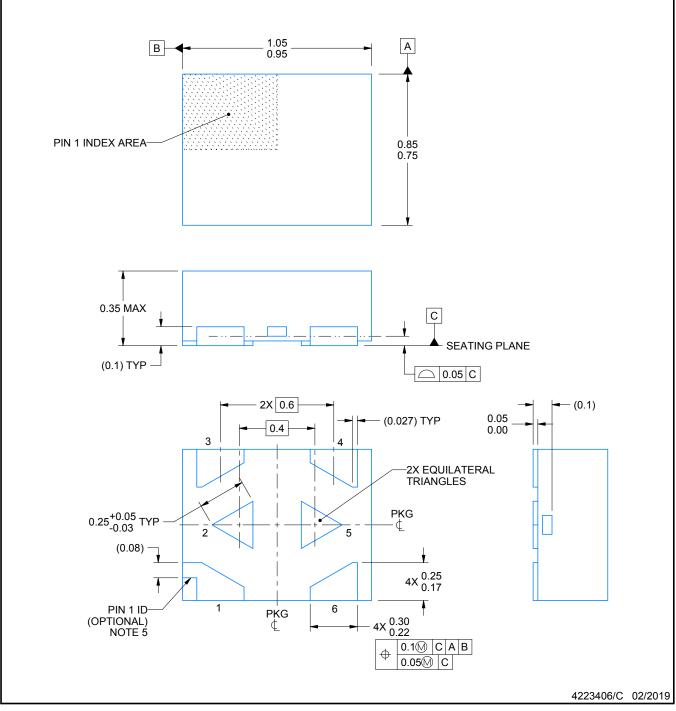
DTB0006A



PACKAGE OUTLINE

X2SON - 0.35 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- The package thermal pads must be soldered to the printed circuit board for optimal thermal and mechanical performance.
 The size and shape of this feature may vary.
- 5. Features may not exist. Recommend use of pin 1 marking on top of package for orientation purposes.

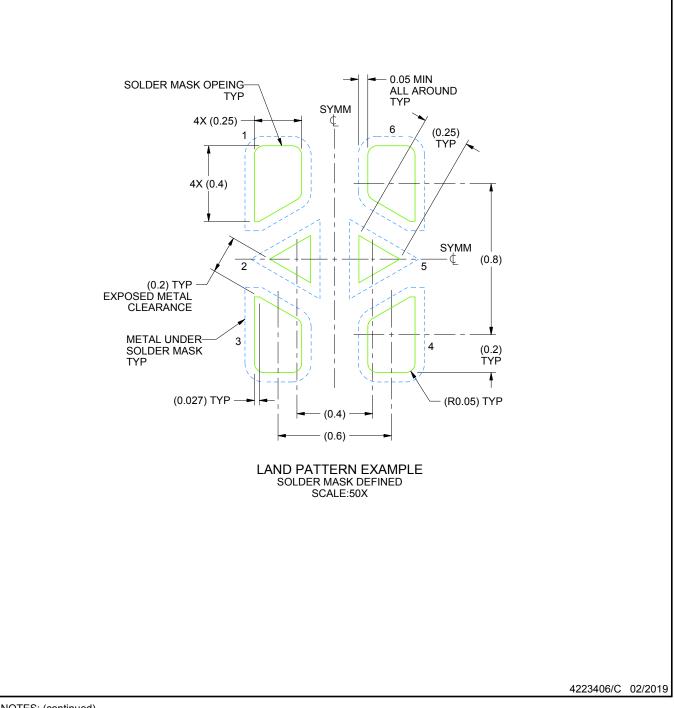


DTB0006A

EXAMPLE BOARD LAYOUT

X2SON - 0.35 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. This package is designed to be soldered to a thermal pads on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

7. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

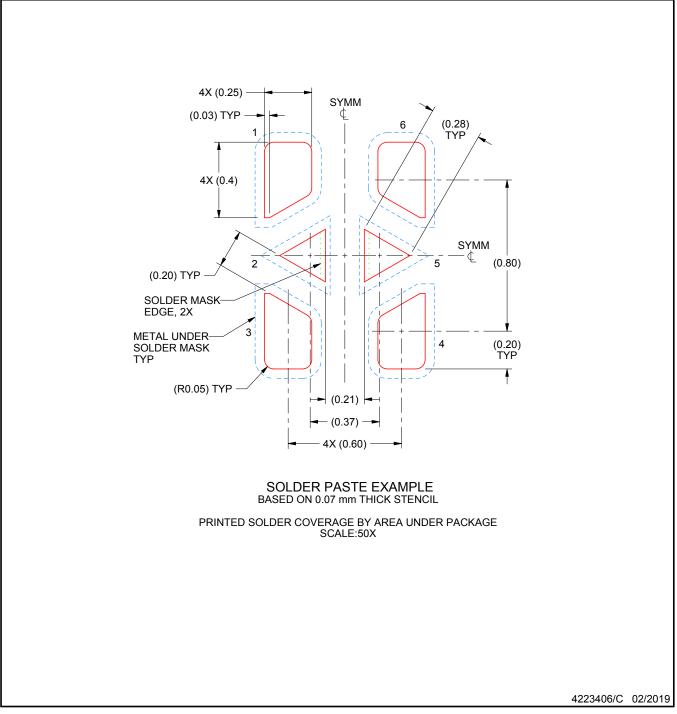


DTB0006A

EXAMPLE STENCIL DESIGN

X2SON - 0.35 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



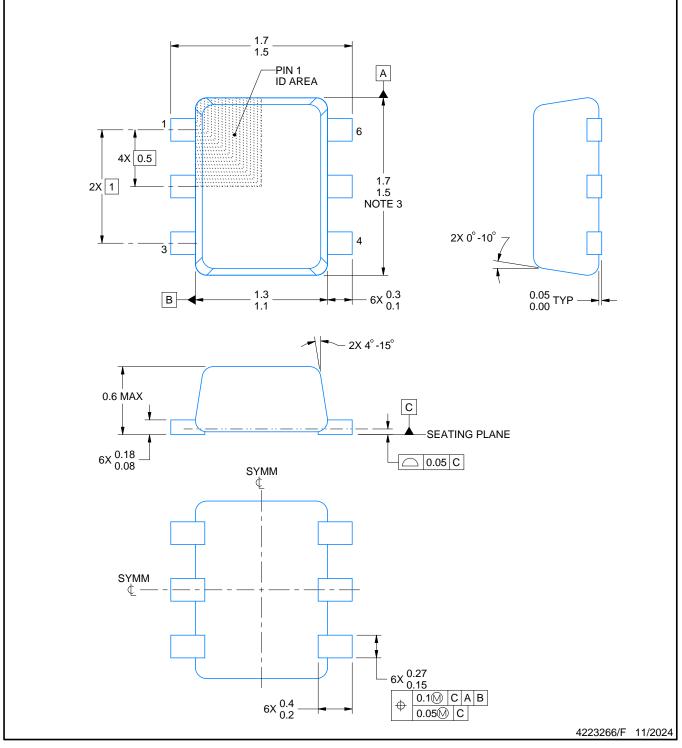
DRL0006A



PACKAGE OUTLINE

SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side. 4. Reference JEDEC registration MO-293 Variation UAAD

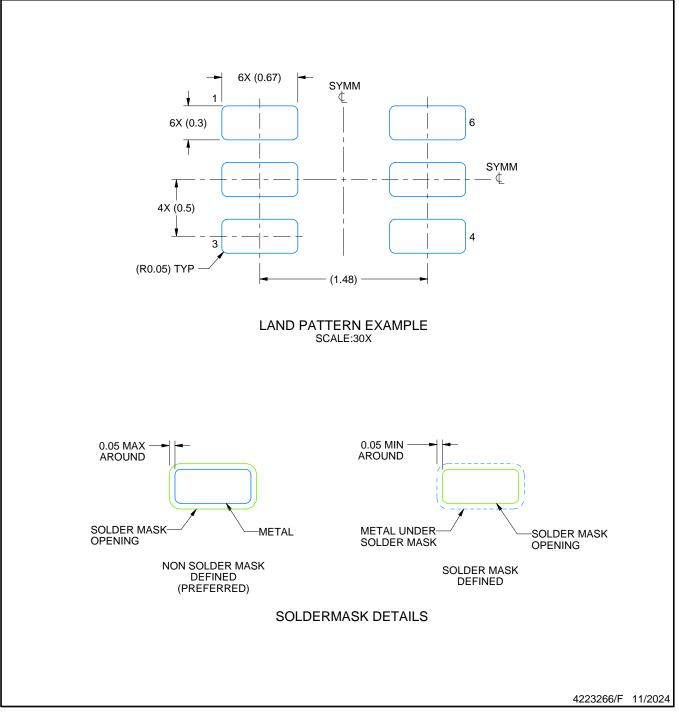


DRL0006A

EXAMPLE BOARD LAYOUT

SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
 7. Land pattern design aligns to IPC-610, Bottom Termination Component (BTC) solder joint inspection criteria.

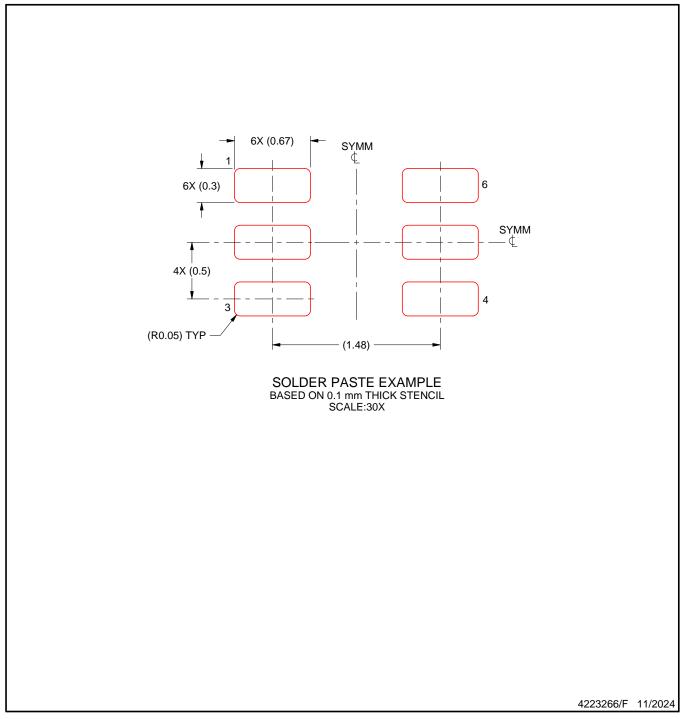


DRL0006A

EXAMPLE STENCIL DESIGN

SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



DBV0006A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.2. This drawing is subject to change without notice.3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- 5. Refernce JEDEC MO-178.



DBV0006A

EXAMPLE BOARD LAYOUT

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DBV0006A

EXAMPLE STENCIL DESIGN

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



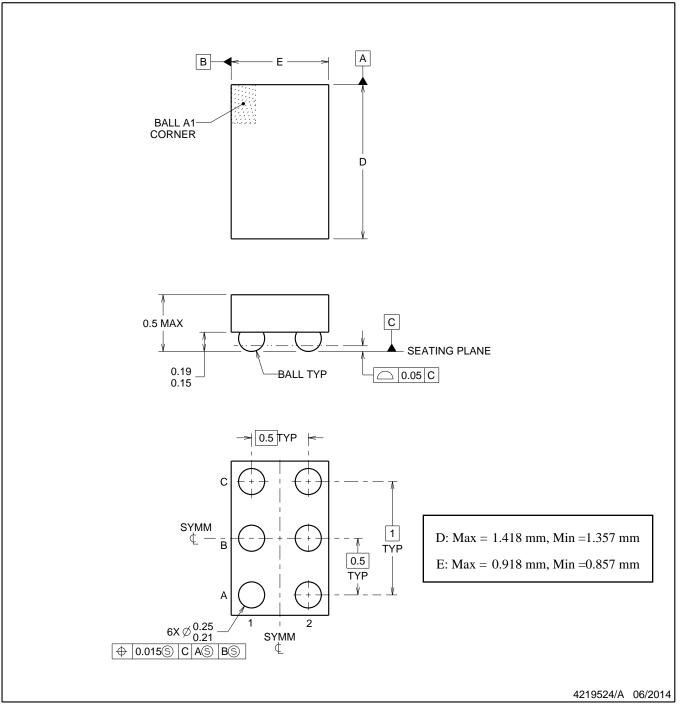
YZP0006



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. NanoFree[™] package configuration.



YZP0006

EXAMPLE BOARD LAYOUT

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



YZP0006

EXAMPLE STENCIL DESIGN

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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